1st run: 30 minute deposition

Prior deposition, test run without wafers was carried out for 30 minutes. Subsequent, undoped n+-polySi deposition took place at 620°C for 30 minutes in the Poly tube with 8 baffles and 1 test wafer with ~1µm of thermal oxide.

WOOLLAM Measurements:
- n+-polySi Thickness: 514.3±0.549 Å
- n+-polySi Roughness: 41.925±0.753 Å
- Oxide Thickness: 9906.5±2.194 Å
- Deposition Rate: 17.1 Å/min

Spectroscopic Ellipsometry $\Psi$ & $\Delta$ data analysis:
10-31-04

2nd run: 60 minute deposition

8 baffles (4 on each side) with 1 test wafers with 1µm of oxide.

n+-polySi Thickness: 1021.3±3.427 Å
n+-polySi Roughness: 49.25±1.62 Å
Oxide Thickness: 9853.4±4.859 Å
Deposition Rate: 17.0 Å/min

Spectroscopic Ellipsometry Ψ & Δ data analysis: